



30V N-Channel NexFET™ Power MOSFET

Check for Samples: CSD17312Q5

FEATURES

- · Optimized for 5V Gate Drive
- Ultra Low Q_g and Q_{gd}
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 5-mm × 6-mm Plastic Package

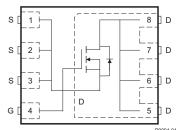
APPLICATIONS

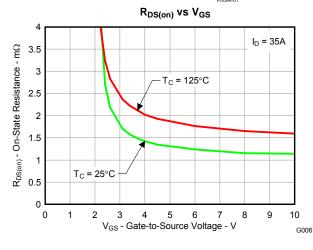
- Notebook Point-of-Load
- Point-of-Load Synchronous Buck in Networking, Telecom and Computing Systems

DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications and optimized for 5V gate drive applications.







PRODUCT SUMMARY

| V _{DS} | Drain to Source Voltage 30 | | | |
|---------------------|-------------------------------|----------------------------|-----|----|
| Q_g | Gate Charge Total (4.5V) 28 | | | nC |
| Q_{gd} | Gate Charge Gate to Drain 6 | | nC | |
| | | $V_{GS} = 3V$ | 1.8 | mΩ |
| R _{DS(on)} | Drain to Source On Resistance | V _{GS} = 4.5V 1.4 | | mΩ |
| | | V _{GS} = 8V 1.2 | | mΩ |
| V _{GS(th)} | Threshold Voltage 1.1 | | V | |

ORDERING INFORMATION

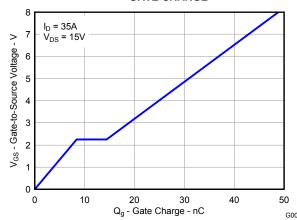
| Device Package | | Media | Qty | Ship |
|----------------|------------------------------------|-----------------|------|------------------|
| CSD17312Q5 | SON 5-mm × 6-mm Plastic Package | 13-Inch Reel | 2500 | Tape and Reel |

ABSOLUTE MAXIMUM RATINGS

| T _A = 2 | 5°C unless otherwise stated | VALUE | UNIT |
|--------------------------------------|--|------------|------|
| V_{DS} | Drain to Source Voltage | 30 | ٧ |
| V_{GS} | Gate to Source Voltage | +10 / -8 | ٧ |
| | Continuous Drain Current, T _C = 25°C | 100 | Α |
| I _D | Continuous Drain Current ⁽¹⁾ | 38 | Α |
| I _{DM} | Pulsed Drain Current, T _A = 25°C ⁽²⁾ | 200 | Α |
| P_D | Power Dissipation ⁽¹⁾ | 3.2 | W |
| T _J , T _{STG} | Operating Junction and Storage Temperature Range | -55 to 150 | °C |
| E _{AS} | Avalanche Energy, Single Pulse $I_D = 130A$, $L = 0.1mH$, $R_G = 25\Omega$ | 845 | mJ |

- (1) Typical $R_{\theta JA}=39^{\circ} C/W$ when mounted on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 0.06-inch (1.52-mm) thick FR4 PCB.
- (2) Pulse duration ≤300µs, duty cycle ≤2%

GATE CHARGE



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

| | PARAMETER | TEST CONDITIONS | MIN TY | P MAX | UNIT |
|---------------------|----------------------------------|--|--------|--------|-----------|
| Static Cl | haracteristics | • | | | |
| BV _{DSS} | Drain to Source Voltage | $V_{GS} = 0V, I_D = 250\mu A$ | 30 | | V |
| I _{DSS} | Drain to Source Leakage Current | $V_{GS} = 0V$, $V_{DS} = 24V$ | | 1 | μΑ |
| I _{GSS} | Gate to Source Leakage Current | $V_{DS} = 0V, V_{GS} = +10/-8V$ | | 100 | nA |
| $V_{GS(th)}$ | Gate to Source Threshold Voltage | $V_{DS} = V_{GS}, I_D = 250 \mu A$ | 0.9 1. | 1 1.5 | V |
| | | $V_{GS} = 3V, I_{D} = 35A$ | 1. | 8 2.4 | $m\Omega$ |
| R _{DS(on)} | Drain to Source On Resistance | $V_{GS} = 4.5V, I_D = 35A$ | 1. | 4 1.7 | mΩ |
| | | $V_{GS} = 8V, I_D = 35A$ | 1. | 2 1.5 | mΩ |
| 9 _{fs} | Transconductance | $V_{DS} = 15V, I_{D} = 35A$ | 20 | 0 | S |
| Dynamic | Characteristics | | | | |
| C _{iss} | Input Capacitance | | 403 | 0 5240 | pF |
| Coss | Output Capacitance | $V_{GS} = 0V, V_{DS} = 15V,$ f = 1MHz | 222 | 0 2890 | pF |
| C _{rss} | Reverse Transfer Capacitance | 1 - 11/11/12 | 9 | 3 120 | pF |
| R _G | Series Gate Resistance | | 1. | 1 2.2 | Ω |
| Qg | Gate Charge Total (4.5V) | | 2 | 8 36 | nC |
| Q_{gd} | Gate Charge Gate to Drain | V _{DS} = 15V, | | 6 | nC |
| Q _{gs} | Gate Charge Gate to Source | I _{DS} = 35A | 8. | 4 | nC |
| Q _{g(th)} | Gate Charge at Vth | | 4. | 4 | nC |
| Q _{oss} | Output Charge | V _{DS} = 14.8V, V _{GS} = 0V | 5 | 7 | nC |
| t _{d(on)} | Turn On Delay Time | | 9. | 5 | ns |
| t _r | Rise Time | $V_{DS} = 15V, V_{GS} = 4.5V,$ | 2 | 7 | ns |
| t _{d(off)} | Turn Off Delay Time | $I_{DS} = 35A$, $R_G = 2\Omega$ | 3 | 5 | ns |
| t _f | Fall Time | | 2 | 3 | ns |
| Diode Cl | haracteristics | | | | |
| V _{SD} | Diode Forward Voltage | I _{SD} = 35A, V _{GS} = 0V | 0. | 8 1 | V |
| Q _{rr} | Reverse Recovery Charge | V _{DD} = 14.8V, I _F = 35A, | 8 | 8 | nC |
| t _{rr} | Reverse Recovery Time | di/dt = 300A/μs | 4 | 3 | ns |
| | | | | | |

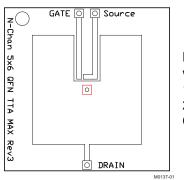
THERMAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

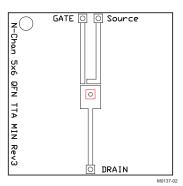
| | PARAMETER | MIN | TYP | MAX | UNIT |
|-----------------|--|-----|-----|-----|------|
| $R_{\theta JC}$ | Thermal Resistance Junction to Case (1) | | | 1 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance Junction to Ambient ⁽¹⁾⁽²⁾ | | | 49 | °C/W |

 $R_{\theta JC}$ is determined with the device mounted on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch x 1.5-inch (3.81-cm x 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. $R_{\theta JC}$ is specified by design, whereas $R_{\theta JA}$ is determined by the user's board design. Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.





Max $R_{\theta JA} = 49^{\circ} C/W$ when mounted on 1 inch² (6.45 cm²) of 2-oz. (0.071-mm thick) Cu.



Max $R_{\theta JA} = 119^{\circ} C/W$ when mounted on a minimum pad area of 2-oz. (0.071-mm thick) Cu.

TYPICAL MOSFET CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

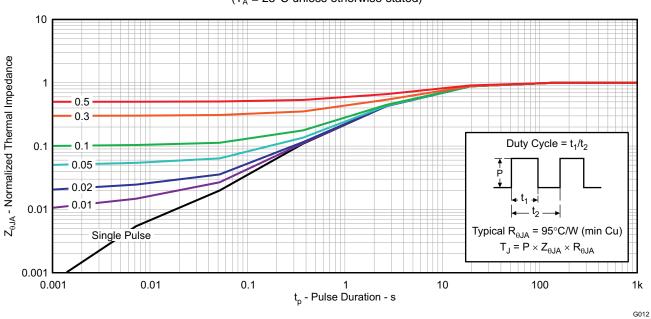


Figure 1. Transient Thermal Impedance



TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

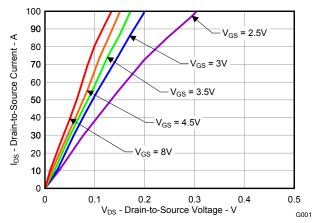


Figure 2. Saturation Characteristics

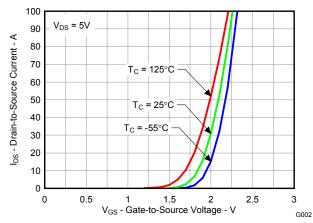


Figure 3. Transfer Characteristics

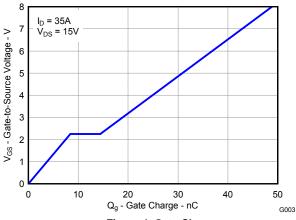


Figure 4. Gate Charge

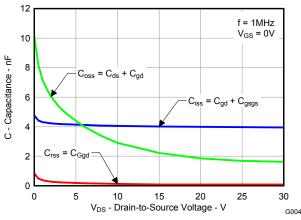


Figure 5. Capacitance

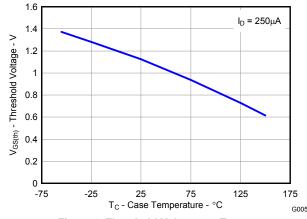


Figure 6. Threshold Voltage vs. Temperature

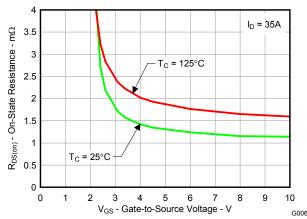


Figure 7. On-State Resistance vs. Gate-to-Source Voltage



TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

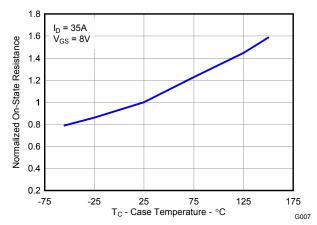


Figure 8. Normalized On-State Resistance vs. Temperature

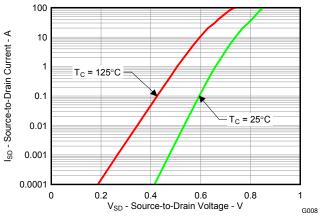


Figure 9. Typical Diode Forward Voltage

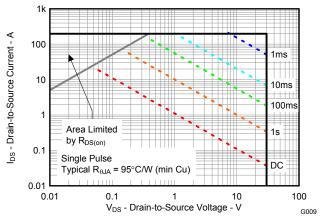


Figure 10. Maximum Safe Operating Area

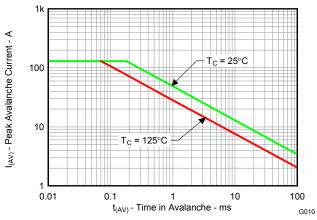


Figure 11. Single Pulse Unclamped Inductive Switching

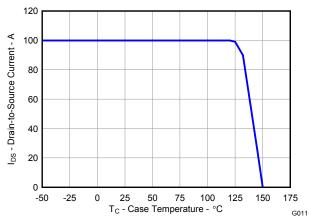
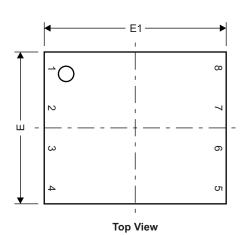


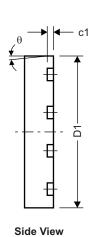
Figure 12. Maximum Drain Current vs. Temperature

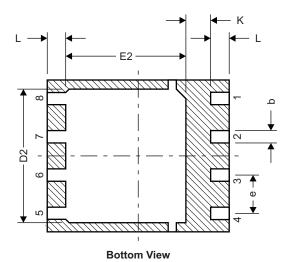


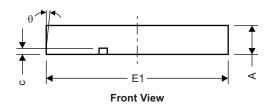
MECHANICAL DATA

Q5 Package Dimensions







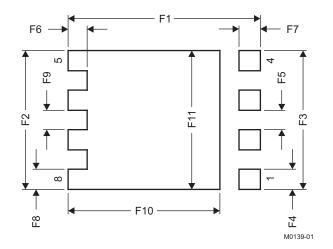


M0140-01

| DIM | MILLIM | ETERS | INCI | HES |
|-----|--------|-------|-------|-------|
| DIW | MIN | MAX | MIN | MAX |
| Α | 0.950 | 1.050 | 0.037 | 0.039 |
| b | 0.360 | 0.460 | 0.014 | 0.018 |
| С | 0.150 | 0.250 | 0.006 | 0.010 |
| c1 | 0.150 | 0.250 | 0.006 | 0.010 |
| D1 | 4.900 | 5.100 | 0.193 | 0.201 |
| D2 | 4.320 | 4.520 | 0.170 | 0.178 |
| Е | 4.900 | 5.100 | 0.193 | 0.201 |
| E1 | 5.900 | 6.100 | 0.232 | 0.240 |
| E2 | 3.920 | 4.12 | 0.154 | 0.162 |
| е | 1.27 | TYP | 0.0 | 50 |
| K | 0.760 | | 0.030 | |
| L | 0.510 | 0.710 | 0.020 | 0.028 |
| θ | 0.00 | | | |



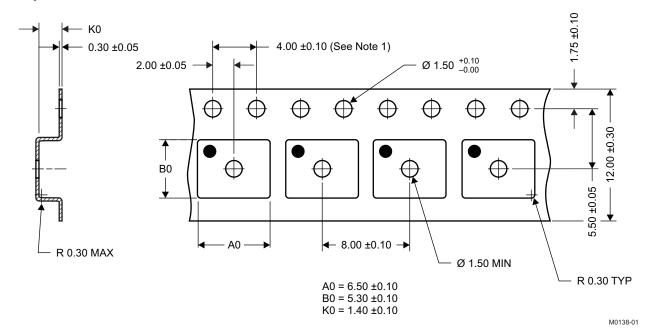
Recommended PCB Pattern



| DIM | MILLIM | ETERS | INC | HES |
|-----|--------|-------|-------|-------|
| DIN | MIN | MAX | MIN | MAX |
| F1 | 6.205 | 6.305 | 0.244 | 0.248 |
| F2 | 4.460 | 4.560 | 0.176 | 0.180 |
| F3 | 4.460 | 4.560 | 0.176 | 0.180 |
| F4 | 0.650 | 0.700 | 0.026 | 0.028 |
| F5 | 0.620 | 0.670 | 0.024 | 0.026 |
| F6 | 0.630 | 0.680 | 0.025 | 0.027 |
| F7 | 0.700 | 0.800 | 0.028 | 0.031 |
| F8 | 0.650 | 0.700 | 0.026 | 0.028 |
| F9 | 0.620 | 0.670 | 0.024 | 0.026 |
| F10 | 4.900 | 5.000 | 0.193 | 0.197 |
| F11 | 4.460 | 4.560 | 0.176 | 0.180 |

For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

Q5 Tape and Reel Information



Notes: 1. 10-sprocket hole-pitch cumulative tolerance ±0.2

- 2. Camber not to exceed 1mm in 100mm, noncumulative over 250mm
- 3. Material: black static-dissipative polystyrene
- 4. All dimensions are in mm, unless otherwise specified.
- 5. Thickness: 0.30 ±0.05mm
- 6. MSL1 260°C (IR and convection) PbF reflow compatible



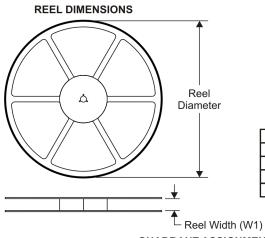
REVISION HISTORY

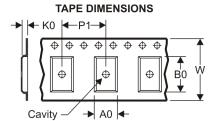
| Cł | hanges from Original (March 2010) to Revision A | Page |
|----|---|------|
| • | Deleted the Package Marking Information section | |

PACKAGE MATERIALS INFORMATION

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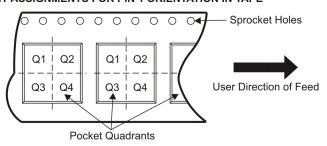
TAPE AND REEL INFORMATION





| | Dimension designed to accommodate the component width |
|----|---|
| B0 | Dimension designed to accommodate the component length |
| K0 | Dimension designed to accommodate the component thickness |
| W | Overall width of the carrier tape |
| P1 | Pitch between successive cavity centers |

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

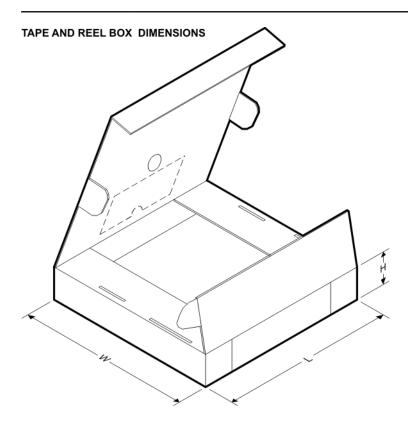


*All dimensions are nominal

| Device | Package Type | Package Drawing | | | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|------------|-----------------|--------------------|---|------|--------------------------|--------------------------|------------|------------|------------|------------|-----------|------------------|
| CSD17312Q5 | SON | DQH | 8 | 2500 | 330.0 | 12.8 | 6.5 | 5.3 | 1.4 | 8.0 | 12.0 | Q1 |

PACKAGE MATERIALS INFORMATION

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*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Length (mm) | Width (mm) | Height (mm) |
|------------|--------------|-----------------|------|------|-------------|------------|-------------|
| CSD17312Q5 | SON | DQH | 8 | 2500 | 335.0 | 335.0 | 32.0 |

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